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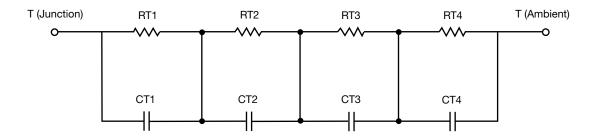
### **R-C Thermal Model Parameters**

#### **DESCRIPTION**

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

#### R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION						
THERMAL RESISTANCE (°C/W)						
Junction to	Ambient	Case	Foot			
RT1	186.4657	N/A	N/A			
RT2	55.8056	N/A	N/A			
RT3	292.8939	N/A	N/A			
RT4	111.6750	N/A	N/A			
	THERMAL CAPACIT	ANCE (Joules/°C)				
Junction to	Ambient	Case	Foot			
CT1	1.6968m	N/A	N/A			
CT2	175.4195u	N/A	N/A			
CT3	4.5286m	N/A	N/A			
CT4	145.2224m	N/A	N/A			

#### Note

N/A indicates not applicable

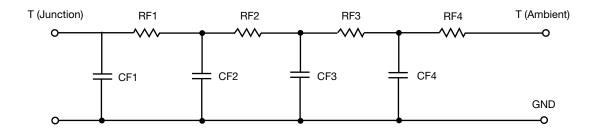
This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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### **R-C THERMAL MODEL FOR FILTER CONFIGURATION**



C VALUES FOR FILTER CONFIGURATION  THERMAL RESISTANCE (°C/W)					
RF1	67.8768	N/A	N/A		
RF2	296.3505	N/A	N/A		
RF3	186.4030	N/A	N/A		
RF4	95.7450	N/A	N/A		
	THERMAL CAPACITA	NCE (Joules/°C)			
Junction to	Ambient N-PCh	Case	Foot		
CF1	163.4479u	N/A	N/A		
CF2	1.0026m	N/A	N/A		
CF3	5.1692m	N/A	N/A		
CF4	146.3402m	N/A	N/A		

Note

N/A indicates not applicable

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